# **DME50B01**

## Silicon PNP epitaxial planar type (Tr1) Silicon NPN epitaxial planar type (Tr2)

For general amplification
DME20B01 in SMini5 type package

#### ■ Features

- High forward current transfer ratio h<sub>FE</sub> with excellent linearity
- $\bullet$  Low collector-emitter saturation voltage  $V_{\text{CE(sat)}}$
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)

#### ■ Marking Symbol: A3

#### ■ Basic Part Number

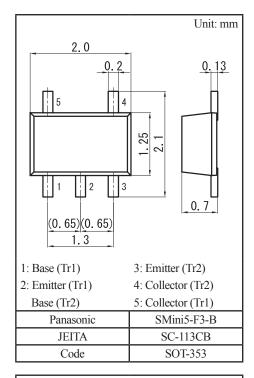
DSA2001 + DSC2001 (Emitterr-base connection)

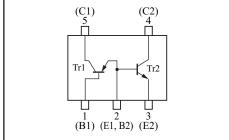
#### Packaging

DME50B010R Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

#### ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter		Symbol	Rating	Unit	
Tr1	Collector-base voltage (Emitter open)	V <sub>CBO</sub>	-60	V	
	Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-50	V	
	Emitter-base voltage (Collector open)	V <sub>EBO</sub>	-7	V	
	Collector current	$I_{C}$	-100	mA	
	Peak collector current	I <sub>CP</sub>	-200	mA	
Tr2	Collector-base voltage (Emitter open)	$V_{CBO}$	60	V	
	Collector-emitter voltage (Base open)	V <sub>CEO</sub>	50	V	
	Emitter-base voltage (Collector open)	$V_{\rm EBO}$	7	V	
	Collector current	$I_{C}$	100	mA	
	Peak collector current	$I_{CP}$	200	mA	
Overall	Total power dissipation	$P_{T}$	150	mW	
	Junction temperature	$T_j$	150	°C	
	Operating ambient temperature	T <sub>opr</sub>	-40 to +85	°C	
	Storage temperature	T <sub>stg</sub>	-55 to +150	°C	





### ■ Electrical Characteristics $T_a = 25$ °C±3°C

#### • Tr1

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_{\rm C} = -10  \mu \text{A}, I_{\rm E} = 0$	-60			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-50			V
Emitter-base voltage (Collector open)	$V_{\mathrm{EBO}}$	$I_E = -10 \mu A, I_C = 0$	-7			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{\rm CB} = -20 \text{ V}, I_{\rm E} = 0$			-0.1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = -10 \text{ V}, I_{B} = 0$			-100	μΑ
Forward current transfer ratio	$h_{FE}$	$V_{CE} = -10 \text{ V}, I_{C} = -2 \text{ mA}$	210		460	_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = -100 \text{ mA}, I_B = -10 \text{ mA}$		- 0.2	-0.5	V
Transition frequency	$f_T$	$V_{CE} = -10 \text{ V}, I_{C} = -2 \text{ mA}$		150		MHz
Collector output capacitance (Common base, input open circuited)	C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		2		pF

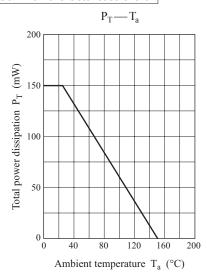
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

#### • Tr2

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = 10 \mu A, I_E = 0$	60			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = 2 \text{ mA}, I_B = 0$	50			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = 10 \mu A, I_C = 0$	7			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = 20 \text{ V}, I_{E} = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = 10 \text{ V}, I_{B} = 0$			100	μΑ
Forward current transfer ratio	$h_{FE}$	$V_{CE} = 10 \text{ V}, I_{C} = 2 \text{ mA}$	210		460	_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$		0.13	0.3	V
Transition frequency	$f_T$	$V_{CE} = 10 \text{ V}, I_{C} = 2 \text{ mA}$		150		MHz
Collector output capacitance (Common base, input open circuited)	C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		1.5		pF

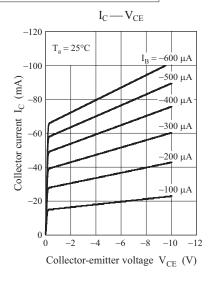
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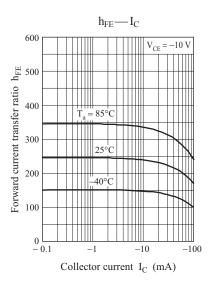
#### Common characteristics chart

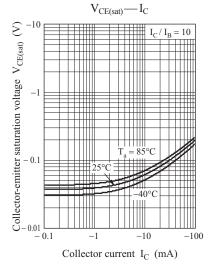


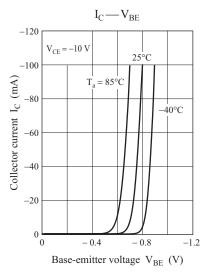
Ver. CED 2

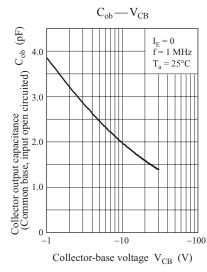
#### Characteristics charts of Tr1

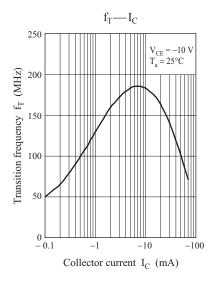




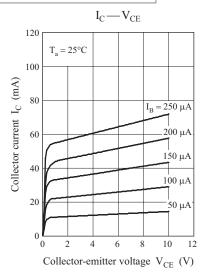


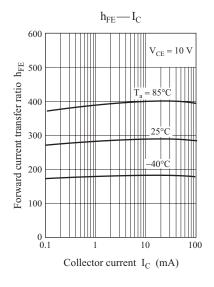


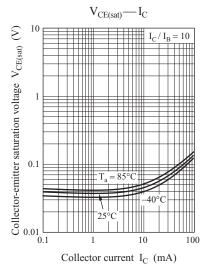




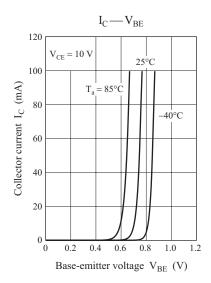
#### Characteristics charts of Tr2

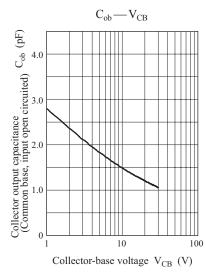


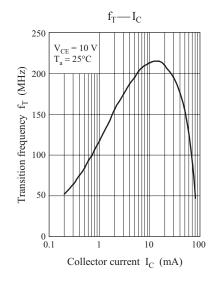




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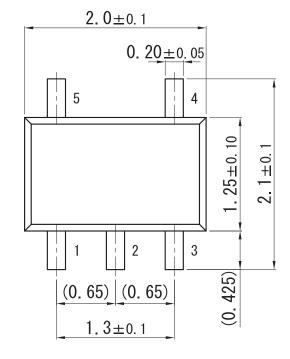


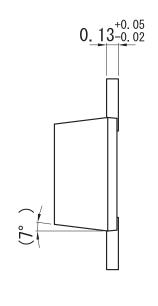


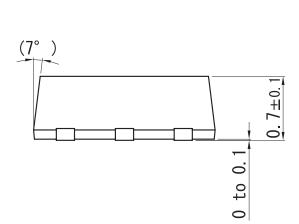
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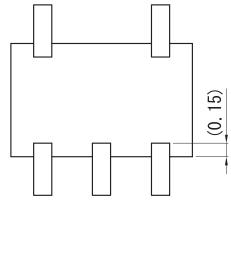
## SMini5-F3-B

Unit: mm

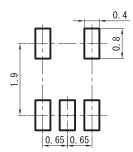








#### ■ Land Pattern (Reference) (Unit: mm)



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